

EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	((phase near10 change) or (resitivity near10 switching) or (variable near10 resistance)) and (memory near5 device) and ((cadmium or cd) near30 (zinc or zn) near30 (n2 or nitrogen))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2010/02/08 11:37
L2	175	((phase near10 change) or (resitivity near10 switching) or (variable near10 resistance)) and (memory near5 device) and ((cadmium or cd) near30 (zinc or zn)) and transmits	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2010/02/08 11:57
L3	286	((phase near10 change) or (resitivity near10 switching) or (variable near10 resistance)) and (memory near5 device) and ((cadmium or cd) near30 (zinc or zn)) and transm\$6	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2010/02/08 11:58
L4	122	((phase near10 change) or (resitivity near10 switching) or (variable near10 resistance)) and (memory near5 device) and ((cadmium or cd) near30 (zinc or zn)) and (transm\$6 near30 light)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2010/02/08 11:58

L5	3	((phase near10 change) or (resitivity near10 switching) or (variable near10 resistance)) and (memory near5 device near30 (transm \$6 near30 light)) and ((cadmium or cd) near30 (zinc or zn))	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2010/02/08 11:59
L6	30	((phase near10 change) or (resitivity near10 switching) or (variable near10 resistance)) and (memory near5 device near30 (transm \$6 near30 light))	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2010/02/08 12:01
S1	294400	((phase near10 change) or (resitivity near10 switching) or (variable near10 resistance))	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2010/02/05 14:57
S2	25876	((phase near10 change) or (resitivity near10 switching) or (variable near10 resistance)) and (memory near5 device)	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2010/02/05 14:57
S3	877	((phase near10 change) or (resitivity near10 switching) or (variable near10 resistance)) and (memory near5 device) and ((cadmium or cd) and (zinc or zn))	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2010/02/05 15:00
S4	2	"US 20090108247"	US-PGPUB; USPAT; USOCR; DERWENT	WITH	ON	2010/02/05 15:01
S5	494	((phase near10 change) or (resitivity near10 switching) or (variable near10 resistance)) and (memory near5 device) and ((cadmium or cd) near30 (zinc or zn))	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2010/02/05 15:09

S6	2	"5271978".did.	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2010/02/05 15:51
S7	2	"0335469".did.	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2010/02/05 15:55
S8	54546	nishida.in.	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2010/02/05 15:57
S10	15	nishida.in. and (((phase near10 change) or (resitivity near10 switching) or (variable near10 resistance)) and (memory near5 device))	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2010/02/05 15:58

2/8/2010 12:54:21 PM

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